

Vishay Siliconix

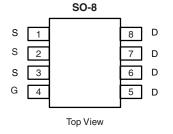
# N-Channel Reduced $Q_g$ , Fast Switching MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)		
30	0.007 at V <sub>GS</sub> = 10 V	16		
	0.010 at V <sub>GS</sub> = 4.5 V	13		

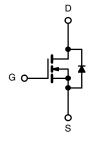
#### FEATURES

- Halogen-free According to IEC 61249-2-21
  Available
- TrenchFET<sup>®</sup> Power MOSFET
- High-Efficiency PWM Optimized
- 100 % R<sub>g</sub> Tested









N-Channel MOSFET

Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30			
Gate-Source Voltage		V <sub>GS</sub>	± 20		V	
	T <sub>A</sub> = 25 °C	– I <sub>D</sub>	16	11	•	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		13	8		
Pulsed Drain Current		I <sub>DM</sub>	± 50		A	
Continuous Source Current (Diode Conduction) <sup>a</sup>		۱ <sub>S</sub>	3.0 1.40		I <sub>S</sub> 3.0	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	Р	3.5	1.6	w	
	T <sub>A</sub> = 70 °C	P <sub>D</sub>	2.2	1.0		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
	t ≤ 10 s	- R <sub>thJA</sub>	29	35	°C/W
Maximum Junction-to-Ambient (MOSFET) <sup>a</sup>	Steady State		65	80	
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	15	18	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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<b>SPECIFICATIONS</b> $T_J = 25^{\circ}$	C, unless o	otherwise noted					
Parameter	Symbol	Test Conditions	litions Min.		Max.	Unit	
Static							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	0.80		1.6	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub> -	$\begin{tabular}{ c c c c c } \hline V_{DS} &= 30 \text{ V}, \text{ V}_{GS} &= 0 \text{ V} \\ \hline V_{DS} &= 30 \text{ V}, \text{ V}_{GS} &= 0 \text{ V}, \text{ T}_{J} &= 70 \text{ °C} \\ \hline \end{tabular}$			1	μA	
					5		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	40			А	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 16 \text{ A}$ $V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 13 \text{ A}$		0.0058	0.007	Ω	
				0.008	0.010		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 16 \text{ A}$		38		S	
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_{S} = 3 \text{ A}, \text{ V}_{GS} = 0 \text{ V}$		0.74	1.1	V	
Dynamic <sup>b</sup>			•	•			
Total Gate Charge	Qg			16.3	24	nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 5.0 \text{ V}, \text{ I}_{D} = 16 \text{ A}$		4			
Gate-Drain Charge	Q <sub>gd</sub>			5.9		1	
Gate Resistance	Rg		0.5	1.5	2.6	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			14	20		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 15 $\Omega$		10	15	ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$\text{I}_\text{D}\cong \text{1}$ A, $\text{V}_\text{GEN}$ = 10 V, $\text{R}_\text{g}$ = 6 $\Omega$		44	70		
Fall Time	t <sub>f</sub>			20	30		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 3 A, dI/dt = 100 A/µs		40	70		

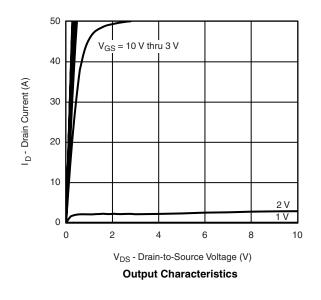
Notes:

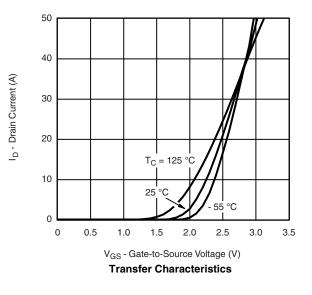
a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



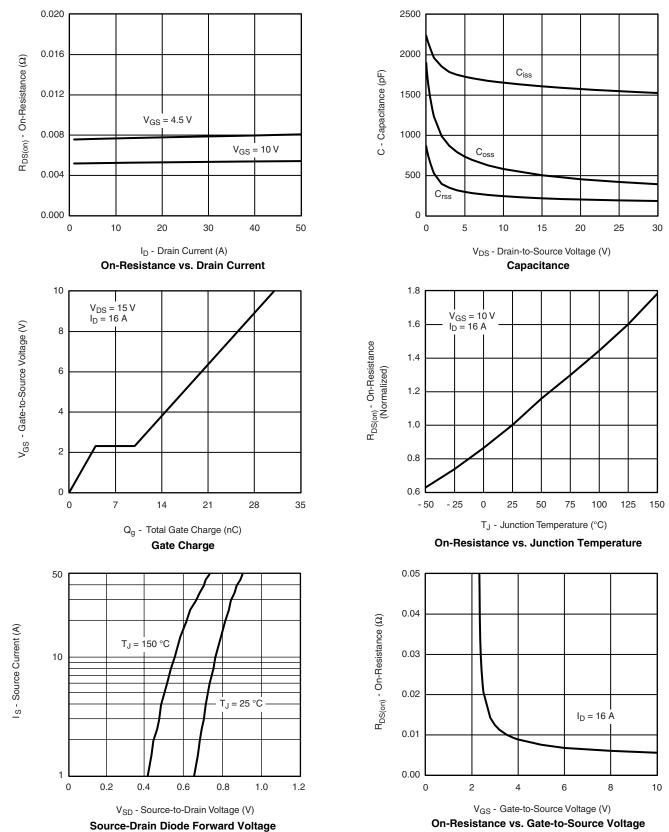


Si4888DY

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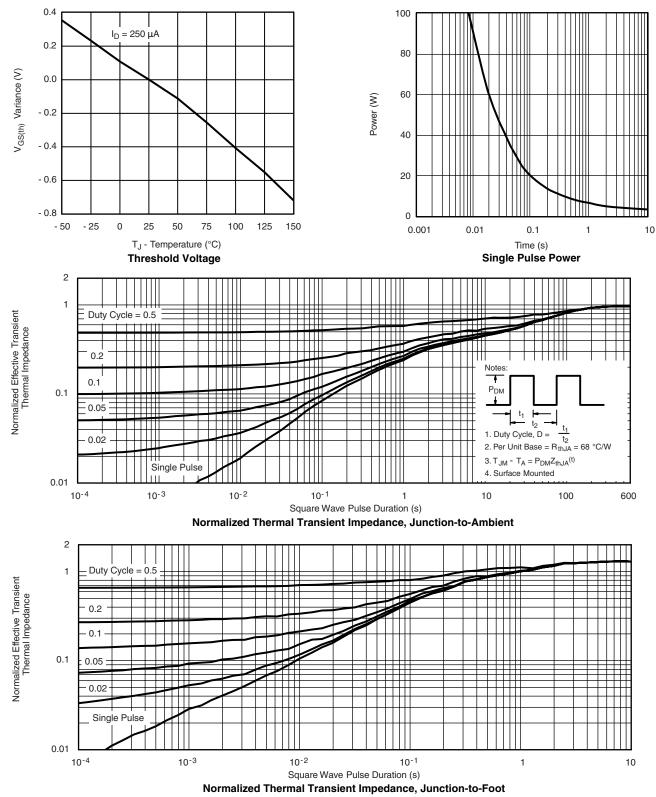


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## Si4888DY

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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?71336">www.vishay.com/ppg?71336</a>.





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